



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_A = +25^\circ C$
50V	$3.5\Omega @ V_{GS} = 10V$	200mA

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- Load switches

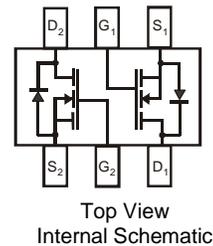


Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed

Mechanical Data

- Package: SOT363
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	NK-BSS138DW	Unit
Drain-Source Voltage	V _{DSS}	50	V
Drain-Gate Voltage (Note 7)	V _{DGR}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 5)	I _D	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	NK-BSS138DW	Unit
Total Power Dissipation (Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	75	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 50V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	1.2	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.4	3.5	Ω	V _{GS} = 10V, I _D = 0.22A
Forward Transconductance	g _{FS}	100	—	—	mS	V _{DS} = 25V, I _D = 0.2A, f = 1.0kHz
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	50	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	8.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	—	20	ns	V _{DD} = 30V, I _D = 0.2A, R _{GEN} = 50Ω
Turn-Off Delay Time	t _{D(OFF)}	—	—	20	ns	

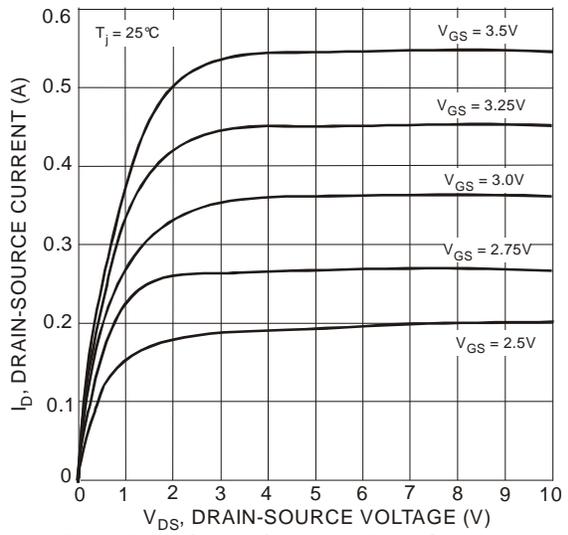


Fig. 1 Drain-Source Current vs. Drain-Source Voltage

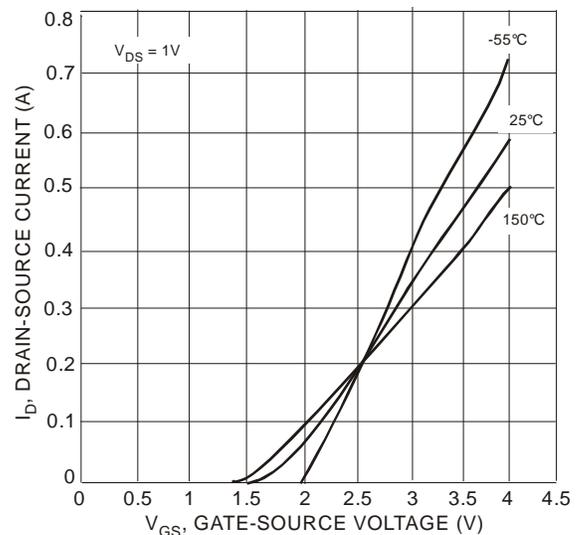


Fig. 2 Transfer Characteristics

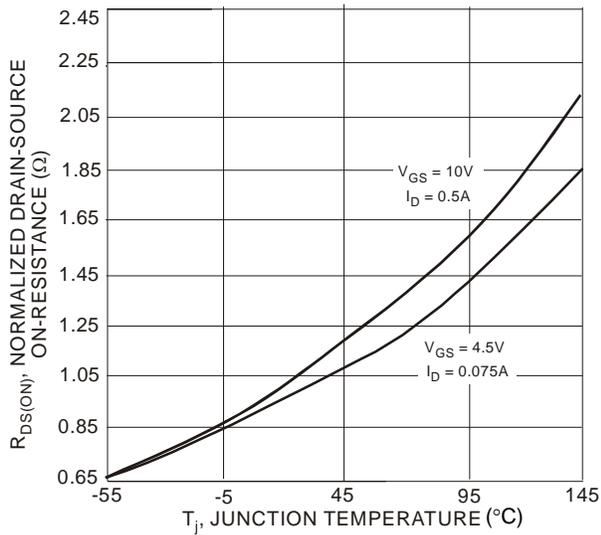


Fig. 3 Drain-Source On Resistance vs. Junction Temperature

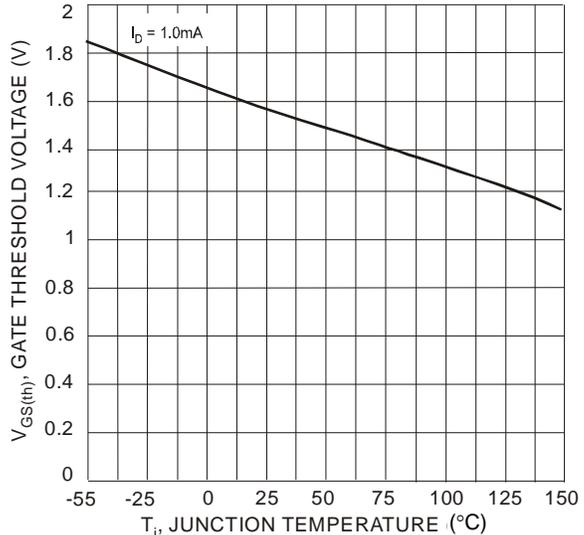


Fig. 4 Gate Threshold Voltage vs. Junction Temperature

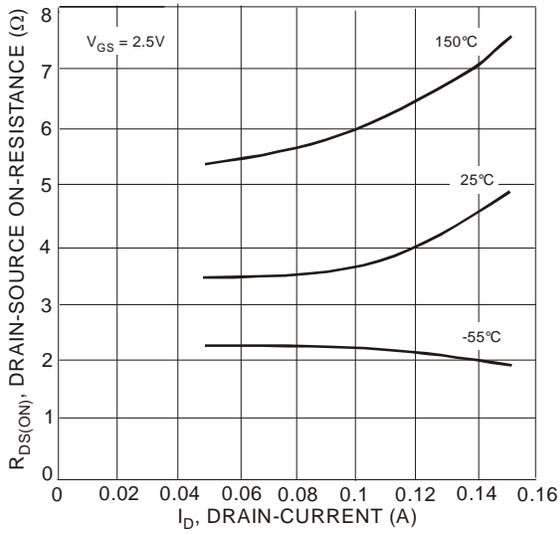


Fig. 5 Drain-Source On-Resistance vs. Drain-Current

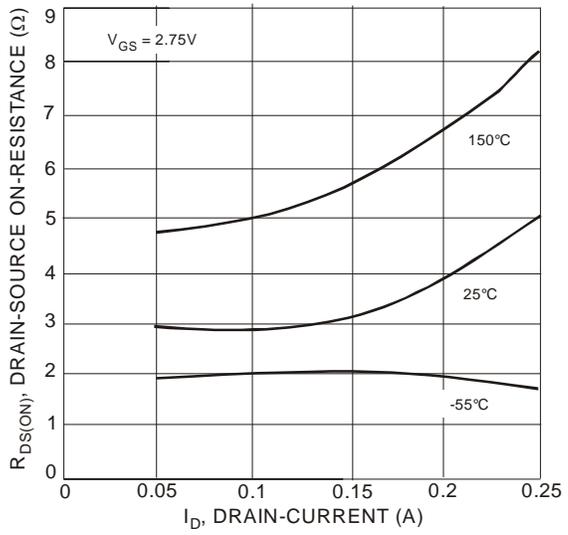


Fig. 6 Drain-Source On-Resistance vs. Drain-Current

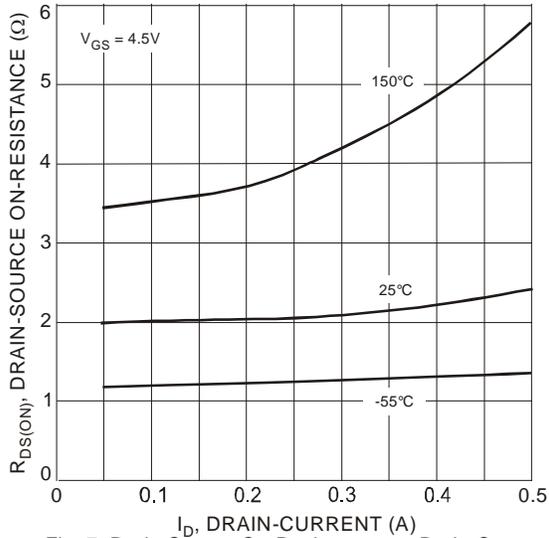


Fig. 7 Drain-Source On-Resistance vs. Drain-Current

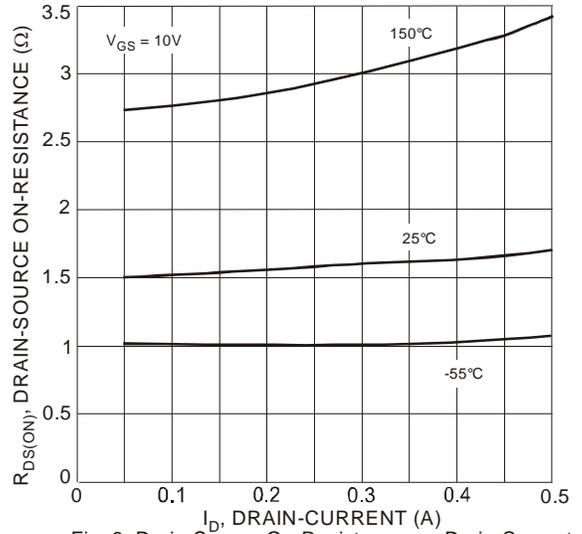


Fig. 8 Drain-Source On-Resistance vs. Drain-Current

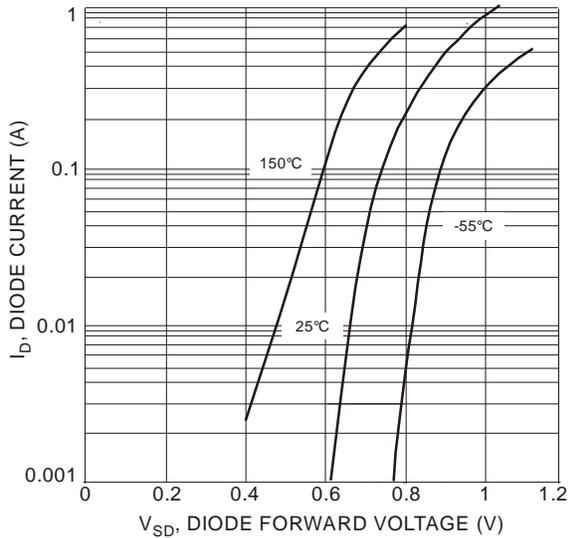


Fig. 9 Body Diode Current vs. Body Diode Voltage

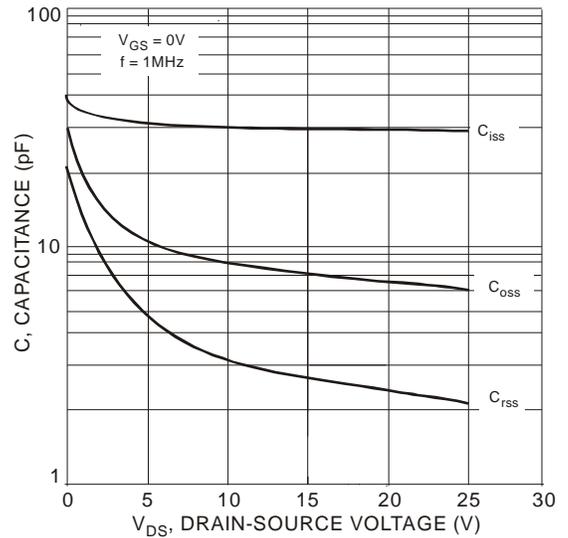
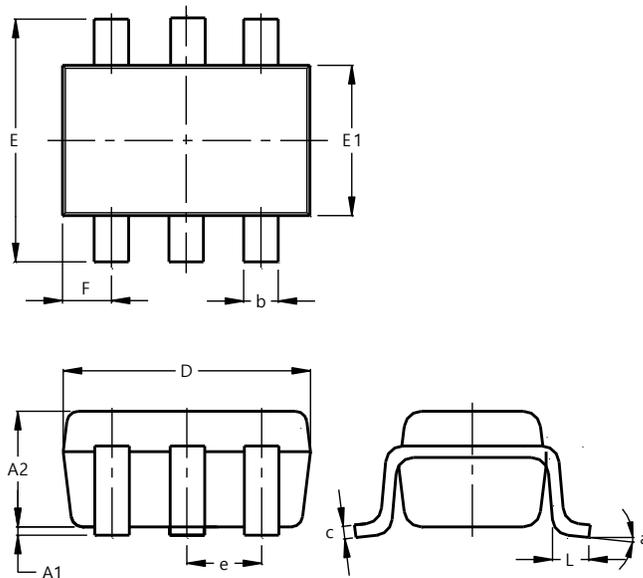


Fig. 10 Capacitance vs. Drain-Source Voltage

Package Outline Dimensions

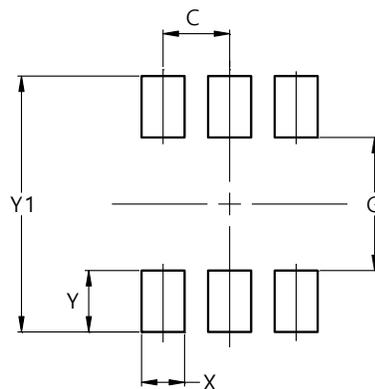
SOT363



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500